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Semiconductor Pinout Informations

H669A Datasheet – NPN Silicon Transistor – Huashan

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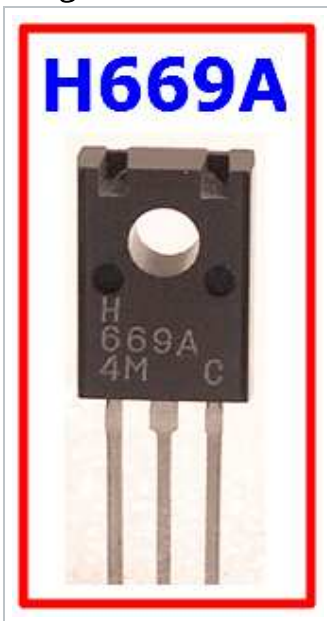
Part Number : H669A

Function : NPN Silicon Transistor (Low-Frequency Power Amplifier)

Package : TO-126ML 3Pin Type

Manufacturers : Huashan

Image :




Description

Limit value ($T_a = 25\text{ }^{\circ}\text{C}$)

1. Storage temperature : $T_{stg} = -55 \sim 150\text{ }^{\circ}\text{C}$
2. Junction temperature : $T_j = 150\text{ }^{\circ}\text{C}$
3. Collector power dissipation ($T_c = 25\text{ }^{\circ}\text{C}$) : $P_C = 20\text{W}$
4. Collector power dissipation ($T_A = 25\text{ }^{\circ}\text{C}$) : $P_C = 1\text{W}$
5. Collector – base voltage : $V_{CBO} = 180\text{V}$
6. Collector – emitter voltage : $V_{CEO} = 160\text{V}$
7. Emitter – base voltage : $V_{EBO} = 5\text{V}$
8. Collector current : $I_C = 1.5\text{A}$

Pinouts

汕头华汕电子器件有限公司		NPN SILICON TRANSISTOR	
		H669A	
		对应国外型号 2SD669A	
主要用途	作低频功率放大。	外形图及引脚排列	
极限值 ($T_a=25^{\circ}\text{C}$)		TO-126ML	
T_{stg} ——贮存温度 $-55\sim 150^{\circ}\text{C}$		
T_j ——结温 150°C	1—发射极, E	
P_C ——集电极功率耗散 ($T_c=25^{\circ}\text{C}$) 20W	2—集电极, C	
P_C ——集电极功率耗散 ($T_A=25^{\circ}\text{C}$) 1W	3—基 极, B	
V_{CBO} ——集电极—基极电压 180V		
V_{CEO} ——集电极—发射极电压 160V		
V_{EBO} ——发射极—基极电压 5V		
I_C ——集电极电流 1.5A		

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